# **Effect of Cerium on the Dielectric and Structural Properties of Barium Titanate-based Ceramics for Multilayer Ceramic Capacitors**

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**Abstract:** Cerium-doped  $BaTi_{1-x}Ce_xO_3$  (x = 0.0, 0.15, 0.25) ceramics were synthesized using the sol-gel auto-combustion technique. An appropriate amount of the chemicals was dissolved in 100ml of distilled water in stoichiometric ratios to form an aqueous solution. The fine barium titanate precursor was pre-calcinated in a digitally controlled muffle furnace at 900°C for 5h. X-ray diffraction (XRD) pattern of the samples indicates that the calcined samples present the formation of a tetragonal crystal structure of  $BaTiO_3$ . The diffraction peaks tend to have cubic symmetry due to Ce doping. The unit cell volume increases rapidly due to Ce doping This is attributed to the substitution of Ce ions at Ti sites, Fourier Transform Infrared Spectroscopy (FTIR) shows a strong absorption peak for pure BT powder is obtained at 484cm<sup>-1</sup>, 485cm<sup>-1</sup> and 487cm<sup>-1</sup> for (x = 0.0, 0.15, 0.25) respectively, hence the bond energy increases with increase in doping concentration. The Field Emission Scanning Electron Microscopy (FESEM) and Energy Dispersive Spectroscopy (EDX) prepared at 1,100 °C for 5 h show a homogeneous particle size of about 50.77nm and 75.87nm for x =0.00 and 0.25, respectively. With Ce doping, a more homogeneous grain size evolved with an increase in average grain size and density with an increase in Ce doping concentration. The EDX spectra show the presence of Ba, Ti, Ce, and O. The result confirms that pure barium titanate is a dominant phase. There is an enhancement in the dielectric constant in the sample with the highest amount of Cerium (x=0.25) characteristic of the copper sample, which is a good material for Multilayer ceramic capacitors.

*Keywords*: Barium titanate; Lattice Constant; Morphology; Dielectric constant; Ceramics

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# **1.0 Introduction**

Rare earth oxides (REOs) and metals are a significant class of materials that have sparked interest in modern technology worldwide. REOs and metals (which include Yb, Er, Sm, Eu, Y, Gd, Dv, and Ce) are primarily used in various chemical and industrial sectors and can improve the dielectric properties of barium titanate (BaTiO<sub>3</sub>)-based ceramics (Hossain et al., 2022; Zhang et al., 2020). Stoichiometric double doping can accelerate the dissolution of a rare-earth element, as each dopant is more soluble due to essentially no ionic defects(A. Kumari & Ghosh, 2018). It has been found that adding a small amount of RE to BaTiO<sub>3</sub> compounds significantly improves their mechanical, dielectric, and synthesis properties, as well as their microstructure and phase structure, while also lowering the transition temperature(Alshoaibi et al., 2020; Ismail et al., 2016).

Despite these advancements, there remains a lack of comprehensive understanding regarding the B-site vacancy compensation model in RE-doped BaTiO<sub>3</sub> ceramics. This study specifically addresses this knowledge gap by investigating the structural and dielectric behaviour of Ce4+-Ce4-substituted BaTiO<sub>3</sub>, where Ce<sup>4+</sup> replaces Ti<sup>4+</sup> in the perovskite lattice. Cerium is particularly interesting due to its ability to stabilize the cubic phase near room temperature, which enhances the material's dielectric tunability and thermal stability; both critical for multilayer ceramic capacitor (MLCC) applications (Y.-M. Zhang et al., 2006; Hwang & Han, 2001).

Cerium greatly lowers the Curie temperature of BaTiO<sub>3</sub>, making cerium-doped dielectric ceramics of practical interest (Cernea et al., 2006). Due to its excellent dielectric, ferroelectric properties and low loss characteristics, BaTiO<sub>3</sub> with a perovskite structure, generalized as A2+B4+O3-, is the most widely used ferroelectric material. It is extensively employed in capacitors and electronic devices such as smartphones, personal computers, and passive components(Kim et al., 2012; Kumari et al., 2015: Sharma et al., 2020).

Over the past few decades, doping BaTiO<sub>3</sub> with RE elements has become a growing field of study(Ganguly *et al.*, 2013). Doping with mid-to-heavy rare-earth elements like Y, Dy, and Ho has proven effective at extending the lifespan of ceramic components(Itoh *et al.*, 2002). Several studies have examined the impact of rare-earth doping, particularly partial substitutions of tetravalent Ce ions for Ti sites, on the dielectric characteristics of BaTiO<sub>3</sub> (Lu *et al.*, 2005).

Cerium is a unique RE element with an electronic configuration of  $4f^1$   $5d^1$   $6s^2$ , allowing it to substitute for Ti ions in BaTiO<sub>3</sub> (Y.-M. Zhang *et al.*, 2006). Its ability to switch between valence states (Ce<sup>3+</sup> and Ce<sup>4+</sup>) makes it attractive for defect engineering. The ionic radii suggest that Ce<sup>3+</sup> exchanges with the dodecahedral coordinated A-site, whereas Ce<sup>4+</sup> enters the octahedrally coordinated B-

site. Ce<sup>4+</sup>, being more stable than Ce<sup>3+</sup>, is generally preferred(Zhao *et al.*, 2020). The valence and ionic radius of replacing ions determine whether doping occurs at the A or B site (Joshi *et al.*, 2014; Petrović *et al.*, 2015). It has been observed that Ce<sup>3+</sup> substitution at Ba<sup>2+</sup> sites consistently lowers the Curie temperature (Tc) of BaTiO<sub>3</sub>, whereas Ce<sup>4+</sup> substitution at Ti<sup>4+</sup> sites has minimal effect on Tc. Thus, Ce can act as a substitute for both Ba and Ti sites depending on the Ba/Ti ratio (Hwang & Han, 2001). On Earth's crust, Ce is the most abundant rare-earth element; more prevalent than copper (Alam *et al.*, 2012).

Structural modifications are typically pursued for two reasons: (1) to raise permittivity and (2) to increase frequency-temperature and dielectric stability close to room temperature ( Zhang *et al.*, 2006). Defects significantly impact the dielectric characteristics of BaTiO<sub>3</sub>-based devices. To reduce electric conductivity induced by defects, various bivalent or trivalent elements have been utilized to replace Ti for charge compensation (Joshi *et al.*, 2014). BaTiO<sub>3</sub> is among the most common ceramic materials used for electronic purposes (A. Kumari & Ghosh, 2018).

adjusting the doping quantity Bv of appropriate rare-earth ions, it is possible to produce ferroelectric materials with a reasonable dielectric constant and minimal dielectric loss (Kim et al., 2012; Kumari et al., 2015). The production of MLCCs with high capacitances using Ce-modified BaTiO<sub>3</sub> offers significant advantages, including enhanced flexural strength. excellent DC bias characteristics, and a tunable dielectric constant-temperature relationship controllable via Ce doping levels (Y.-M. Zhang et al., 2006; Kim et al., 2012).

Studies have shown that Ce doping enhances the dielectric constant while maintaining low dielectric loss (tan  $\delta$ ) at low frequencies, essential for minimizing energy dissipation and ensuring efficient capacitor performance(Beena & Jayanna, 2019; Arshad



*et al.*, 2020). Moreover, Ce substitution at Ti sites stabilizes the crystal structure and reduces the tetragonality of BaTiO<sub>3</sub>, promoting a cubic-to-tetragonal phase transition near room temperature. This allows for better temperature stability and improved dielectric tunability, both critical for MLCC applications(Zhang *et al.*, 2006).

Additionally, Ce doping leads to a more homogeneous microstructure with increased grain size and density, as evidenced by FESEM analysis, which contributes to improved mechanical integrity and reduced leakage currents(Mitic *et al.*, 2010). The observed increase in bond energy—as indicated by FTIR peak shifts—further supports greater thermal and chemical stability, making Ce-doped BaTiO<sub>3</sub>suitable for use in harsh environments(Kim *et al.*, 2012).

The combination of high dielectric constant, low loss, controlled temperature dependence, and improved structural and electrical properties makes Ce-modified BaTiO<sub>3</sub> a highly suitable material for next-generation MLCCs requiring miniaturisation, high performance, and long-term reliability.

The main purpose of this research is the synthesis and characterization of B-site deficient Ce rare-earth doped BaTiO<sub>3</sub> with chemical compositions BaTi<sub>1-x</sub>Ce<sub>x</sub>O<sub>3</sub> (x = 0.0, 0.15, 0.25). In this paper, we study the role of an individual Ce dopant on the structural and morphological properties of BaTiO<sub>3</sub>-based ceramics.

# 2.0 Materials and Methods

# 2.1 Chemicals and Reagents

The chemicals and reagents used are highpurity (99%–99.5%) analytical reagents (AR grade). The chemicals include barium nitrate [Ba (NO<sub>3</sub>)<sub>2</sub>] (Loba Chemie), titanium dioxide (TiO<sub>2</sub>) (Loba Chemie), cerium nitrate [Ce (NO<sub>3</sub>)<sub>2</sub>] (CDH), citric acid (C<sub>6</sub>H<sub>8</sub>O<sub>7</sub>) (Loba Chemie), with distilled water as the solvent. All the chemicals and reagents were used as received without any further purification.



# 2.2 Experimental Details

Synthesis of Ce<sup>4+</sup> substituted BaTiO<sub>3</sub> with chemical composition  $BaTi_{1-x}Ce_xO_3$  (x = 0.0, 0.15, 0.25) has been successfully synthesized using sol-gel technique. An appropriate amount of the chemicals was dissolved in 100ml of distilled water in stoichiometric ratios to form an aqueous solution. The molar ratio of citric acid to cation was maintained at 1:2. The prepared solution was heated at a temperature of 80-100°C. The solution was stirred using constant and continuous magnetic stirring in order to evaporate the water; a white gel was obtained, which was transferred to a hot plate and heated at a temperature of 280-300 °C. This gives a black precursor material which was ground with a mortar and pestle to obtain a fine precursor which barium titanate was precalcinated in a digitally controlled muffle furnace at 900°C for 5 h. The pre-calcinated powder was divided into three parts and labelled MA1, MA2, and MA3. Furthermore, MA1, MA2 and MA3 were further heated at 1100°C for 5 h. The obtained product was crushed using a mortar and pestle to obtain the fine barium titanate ceramic powder, followed by various characterizations.

# 2.3 Characterization

Structural and phase analysis were carried out with a Bruker AXS D8 advanced XRD diffractometer. Functional groups were also evaluated from FTIR spectra obtained with a Nicolet FTIR interferometer infrared Prestige-21 (model 8400S). The morphology and elemental analysis were studied using FESEM/energy-dispersive X-ray (EDX) spectroscopy (FEI Nova NanoSEM 450 FE-SEM) at a voltage of 15KV.

# 3.0 Results and discussion

# 3.1 XRD analysis

The XRD patterns of  $BaTi_{1-x}Ce_xO_3$  (x = 0.0, 0.15, 0.25) are shown in Fig. 1. The diffraction peaks observed were indexed using JCPDS card number 79-2263 (Hai *et al.*, 2014). The calcined samples present the

formation of the tetragonal crystal structure of BaTiO<sub>3</sub>. Because of the doping of Ce, the diffraction peaks frequently exhibit cubic symmetry. As evidenced by the quick rise in unit cell volume caused by Ce doping (Table 1). This is attributed to the replacement of Ce ions at Ti sites because the skeleton of a perovskite structure is made up of TiO, octahedra, and the 6-coordinate Ce<sup>4+</sup> ionic radius (0.087 Å) is larger than the Ti<sup>4+</sup> ionic radius ( 0.0605 Å). (Chemistry, 2006). The lattice constant (a) and the volume of the unit cell (V<sub>cell</sub>) were calculated using Equations (1) and (2).

 $a = d\sqrt{h^2 + k^2 + l^2}$  (1)  $V_{cell} = a^3$  (2)

where d is the interplanar spacing, h, k and l are the Miller indices. The lattice constant, the interplanar spacing and the volume of the unit

cell are shown in Table 1. From the calculated table, it was found that the lattice constant increases with an increase in Ti-Ce concentrations, likewise, the volume of the unit cell increases with an increase in Ti-Ce concentrations. We assume the lattice grows when rare earth ions (RE) are present on the B-site and contracts when RE are present on the A-site and when there are vacancies(Tsur *et al.*, 2001).

Table 1: Lattice Parameters and Unit Cell Volume of Ba (Ti  $_{1-x}$  Ce<sub>x</sub>) O<sub>3</sub> for (hkl) = (110)

X	0.00	0.15	0.25
d (Å)	2.8232	2.8234	2.8238
a (Å)	3.9926	3.9928	3.9934
Vcell	63.6454	63.6550	63.6837
(Å <sup>3</sup> )			



Fig, 1: XRD patterns of BaTi1-xCexO3 (x = 0.0, 0.15, 0.25)

The spectra indicate the predominant presence of doped perovskite cubic phase with a cell parameter of 3.9926 Å and space group P4mm, for (110) Miller indices. Since the radius of the Ce ion is bigger than titanium, when cerium is incorporated at the B-site, a more closely packed  $BO_6$  octahedral is achieved with enhanced thermal stability. Although this doping causes structural distortion, it also results in a decrease in the oxygen octahedron



interstices, which strengthens the octahedra (Ganguly *et al.*, 2013). The existence of the RE element in the powder is shown by the peak's inclusion in the XRD spectra. Ion replacement with BaTiO<sub>3</sub> causes the second phase to coincide. (Joshi et al., 2015). The expansion of sites with larger Ce ions in the BaTiO<sub>3</sub> host lattice, as shown in Fig. 1 (\$, and #), is responsible for the large XRD peaks shifts to the low angle of BaTiO<sub>3</sub>, demonstrating that Ce doping causes a larger lattice strain and further destroys the long-range order of the BaTiO<sub>3</sub> lattice. as reported by (Lu *et al.*, 2007). The charge balance compensation mechanism may be described as follows:

 $BaO + CeO_2 \rightarrow Ba_{Ba} + CeTi + 3O_2$ 

The impurities in the starting materials and the defects are composed of  $Ce^{4+}$  ions at the Ti sites (CeTi)

## 3.2 FTIR analysis

Fig 2 shows the FTIR spectra of  $BaTi_{1-x}Ce_xO_3$ (x = 0.0, 0.15, 0.25) in the wave number range 500-4000 cm<sup>-1</sup>. To examine the impact of additions in the ceramic, the FTIR method was used. FTIR is a useful tool to investigate the relationship between the physical characteristics and microstructure of perovskite ferroelectric materials since the ferroelectricity in these materials is highly dependent on the vibration of the crystal lattice. Due to its sensitivity to chemical bonding, FTIR is a crucial technology for studying the reaction process used in the creation of materials. (Kumari & Ghosh, 2018). A strong absorption peak for pure BT powder is obtained at 484cm<sup>-</sup> , 485 cm<sup>-1</sup> and 487 cm<sup>-1</sup> for (x = 0.0, 0.15, 0.25), respectively. This mode is crucial because the spontaneous polarization in BT with the tetragonal phase runs parallel to the direction of stretched normal vibration, as seen in (Ganguly, Rout, Park, et al., 2013). Another peak is observed at 1424cm<sup>-1</sup>, 1436cm<sup>-1</sup>, and 1445 cm<sup>-1</sup> for (x = 0.0, 0.15, 0.25), respectively. A shift of absorption peaks for the stretching normal vibration of Ti-O octahedron towards higher energy is observed. Hence, the bond energy increases with an increase in doping concentration.





## 3.3 FESEM analysis

FESEM and EDS were used to analyze the material's surface morphology (Hossain *et al.*, 2022) Fig, 3 (a) and (c) show the field emission scanning electron microscopy micrographs of the sample BaTi<sub>1-x</sub>Ce<sub>x</sub>O<sub>3</sub> (x = 0.0 and 0.25), prepared at 1,100 °C for 5 h. The fired powders of (Ba, Ce) TiO<sub>3</sub> solid solution show homogeneous particle sizes of about

50.77nm and 75.87nm for x = 0.00 and 0.25, respectively. With Ce doping, a more homogeneous grain size evolved with an increase in average grain size and density with an increase in doping concentration. Neither any kind of microcrack nor any kind of pore is identified anywhere, as reported by (Ganguly, Rout, et al., 2013)



Fig, 3: FESEM micrograph and particle distribution of BaTi1-xCexO3 (x = 0.00, and 0.25).

It is clearly evident that all pellets are highly dense, Ce-doped polycrystalline ceramics have larger grain sizes than undoped polycrystalline ceramics (Zhong *et al.*, 2005). The pure  $BaTiO_3$  ceramics were not uniform in grain size distribution and some large grains were observed, which can affect the electric properties of  $BaTiO_3$  ceramics strongly (Joshi



*et al.*, 2014). Though it was reported that in some instances  $BaTi_{1-x}Ce_xO_3$  ceramics show an inhomogeneous grain size distribution (Zhang *et al.*, 2006). Also Morphological tudy shows that the addition of rare-earth ions affects the growth of the grain and remarkably changes the grain morphology as reported by

(Feng *et al.*, 2012). With the doping of additives, the grains became smaller, the density became higher, and the cracks and pores accumulation gradually disappeared. The EDX spectra show the presence of Ba, Ti, Ce, and O. The result confirms that pure barium titanate is a dominant phase.



Fig. 4: EDX spectra and mapping of BaTi1-xCexO3 (x = 0.00 and 0.25)



#### 3.4 Dielectric Analysis

The dielectric properties of Ce-doped BaTiO<sub>3</sub> ceramics were investigated by measuring the real part of the dielectric permittivity ( $\epsilon'$ ), dielectric loss tangent (tan  $\delta$ ), and AC conductivity as functions of frequency. These

measurements provide insight into the polarization mechanisms, defect structure, and conduction behavior of the material, which are critical for MLCC applications.



Fig, 5: Room temperature Dielectric constant of BaTi<sub>1-x</sub> Ce<sub>x</sub>O<sub>3</sub> (x = 0.00, 0.15, and 0.25)

From Fig.5, it is clearly observed that the dielectric constant ( $\varepsilon'$ ) increases with an increase in cerium (Ce) doping concentration, particularly at low frequencies. The highest recorded value of the dielectric constant,  $\varepsilon' = 6700$ , was observed for the sample with x = 0.25 at a frequency of 30 Hz. This significant enhancement in dielectric response can be attributed to several interrelated factors.

Firstly, the substitution of Ce<sup>4+</sup> ions at the Ti<sup>4+</sup> sites within the perovskite structure leads to lattice expansion, as evidenced by the increase in unit cell volume reported in Table 1. This expansion enhances the polarizability of the lattice, thereby increasing the dielectric



constant. Secondly, structural analysis using X-ray diffraction (XRD) reveals a transition from a tetragonal to a pseudo-cubic symmetry with increasing Ce content. This structural transformation tends to lower the Curie temperature closer to room temperature and broadens the temperature range over which high dielectric constant values are sustained. Such behavior is consistent with previous reports (Y.-M. Zhang et al., 2006; Ganguly et 2013). and it implies improved al.. stability temperature in the dielectric performance of the material.

Additionally, at lower frequencies, the dielectric response is significantly influenced

by interfacial polarization, dipolar relaxation, and space charge accumulation. These polarization mechanisms become more pronounced in the Ce-doped samples due to the reduction in oxygen vacancies and the improvement in microstructural homogeneity. Studies by Beena & Jayanna (2019) and Mitic et al. (2010) support this observation, suggesting that Ce doping optimizes defect chemistry and charge distribution within the grains and at the grain boundaries.

Furthermore, Fourier Transform Infrared (FTIR) spectroscopy results, as shown in Figure 2, exhibit a blue shift in absorption peaks with increasing Ce concentration. This spectral shift is indicative of stronger Ce–O bonding and a corresponding increase in bond energy, which contributes to improved chemical and thermal stability. Such stability further reinforces the material's ability to

sustain high dielectric constants (Kim et al., 2012; Kumari et al., 2015).

Finally, microstructural analysis using Field Emission Scanning Electron Microscopy (FESEM), presented in Figure 3, shows that Ce doping results in the formation of larger and more uniform grains. The reduction in grain boundary defects facilitates easier domain wall motion, which plays a crucial role in enhancing polarization behavior and thereby increasing the dielectric constant. This observation is consistent with previous findings by Feng et al. (2012) and Zhong et al. (2005), who reported similar correlations between grain size and dielectric performance. In summary, the observed increase in  $\varepsilon'$  with Ce doping is a synergistic outcome of lattice expansion, structural transitions, enhanced polarization mechanisms, stronger chemical bonding, and improved microstructural characteristics.



Fig., 6: Room temperature Dielectric loss tangent of BaTi1-xCexO3 (x = 0.00, 0.15, and 0.25).



Regarding dielectric loss (tan  $\delta$ ), Fig. 6 shows a decrease at low frequencies with Ce doping, suggesting lower leakage currents and fewer defect-induced conduction paths. This aligns with previous findings that Ce<sup>4+</sup> substitution

effectively compensates for B-site vacancies and reduces oxygen deficiency(Lu et al., 2007; Petrović et al., 2015). However, tan δ increases sharply at high frequencies, likely due to enhanced ionic mobility or electrode polarization effects.



Fig. 7: Room temperature AC conductivity of BaTi1-xCexO3 (x = 0.00, 0.15, and 0.25) The alternating current (AC) conductivity measurements presented in Figure 7 reveal distinct frequency-dependent behavior characteristic of dielectric ceramics. At low frequencies, the conductivity exhibits a nearly frequency-independent trend. This behavior is typically associated with hopping conduction or band transport mechanisms, where localized charge carriers move between defect states or through narrow energy bands. As the frequency increases, the conductivity begins to rise more noticeably. which can be attributed to phenomena such as ionic relaxation or

electrode polarization. These effects are common in dielectric materials where mobile ions respond to the alternating field but cannot follow rapid changes at higher frequencies. The observed increase in AC conductivity with frequency in the Ce-doped BaTiO<sub>3</sub> samples aligns well with previous studies (Beena & Jayanna, 2019) and supports the potential of these materials for high-frequency electronic applications.

Taken together, the dielectric and electrical behaviors observed in this study provide compelling evidence that Ce doping has a

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multifaceted positive effect on BaTiO<sub>3</sub>. It not only improves the structural and morphological characteristics of the ceramic matrix but also enhances its electrical properties. The combination of high dielectric constant, stable conductivity response, and structural integrity makes Ce-doped BaTiO<sub>3</sub> a strong candidate for use in advanced multilayer ceramic capacitors (MLCCs) and related high-performance electronic devices.

In summary, the incorporation of Ce<sup>4+</sup> into the BaTiO<sub>3</sub> lattice improves the dielectric constant  $(\varepsilon')$  and overall electrical performance through several interconnected mechanisms. The substitution of Ce4+ for Ti4+ leads to a measurable expansion of the unit cell, increasing the material's polarizability. Structural analysis confirms that this doping induces a shift from the tetragonal to pseudocubic phase, effectively lowering the Curie temperature toward room temperature. This structural adjustment enables the material to maintain high dielectric values over a broader temperature range.

Moreover, Ce doping enhances polarization phenomena, particularly at low frequencies, by promoting the formation of defect dipoles and increasing space charge accumulation. FTIR spectral shifts indicate stronger Ce–O bonding, which contributes to improved lattice stability and facilitates ionic displacement. Microstructural examinations reveal that Ce inclusion promotes grain growth, resulting in larger and more uniform grains that reduce internal defects and improve domain wall mobility.

Finally, the doped system exhibits reduced oxygen vacancy concentration and leakage currents, indicating effective defect compensation. This not only stabilizes the dielectric behavior but also contributes to the reliability and longevity of the material under electrical stress. Altogether, these enhancements underscore the suitability of Cedoped BaTiO<sub>3</sub> for next-generation capacitive devices, confirming its potential as a highly



functional material for miniaturised and highefficiency electronic components.

# 4.0 Conclusion

The study comprehensively investigated the structural, microstructural, and dielectric properties of Ce4+-doped BaTiO<sub>3</sub> ceramics synthesized via the sol-gel auto-combustion method. X-ray diffraction analysis confirmed that increasing Ce content induces a transition from a tetragonal to a pseudo-cubic phase, accompanied by lattice expansion and an increase in unit cell volume, attributed to the substitution of larger Ce4+ ions at Ti4+ sites. FTIR spectroscopy revealed a blue shift in peaks with absorption higher Ce concentrations, indicating stronger Ce-O bonding and increased bond energy, which enhance the material's chemical and thermal stability. Microstructural analysis using FESEM showed that Ce doping leads to the formation of larger, more uniform grains, resulting in improved density, reduced defects, and enhanced homogeneity of the ceramic matrix. Dielectric measurements demonstrated a marked increase in the dielectric constant, reaching a maximum value of  $\varepsilon' = 6700$  at 30 Hz for the x = 0.25 composition, alongside a reduction in dielectric loss at low frequencies. AC conductivity studies indicated frequencyindependent behavior at low frequencies and a frequency-dependent increase at higher frequencies, with multiple consistent conduction mechanisms. findings These collectively establish that Ce doping significantly improves the dielectric, structural, and morphological characteristics of BaTiO<sub>3</sub>, making it a strong candidate for advanced multilayer ceramic capacitor (MLCC) applications123.

In conclusion, the incorporation of  $Ce^{4+}$  into the BaTiO<sub>3</sub> lattice enhances the material's polarizability, stabilizes its structure, and optimizes its dielectric performance through synergistic effects on lattice parameters, defect chemistry, and grain morphology. The observed improvements in dielectric constant,

reduced loss, and structural integrity confirm the suitability of Ce-doped BaTiO<sub>3</sub> for use in miniaturized and high-efficiency electronic components123.

Based on these results, it is recommended that further research explore the optimization of Ce doping levels and processing conditions to maximize performance for specific electronic applications. Additionally, investigating the long-term reliability and temperature stability of Ce-doped BaTiO<sub>3</sub> in device-relevant environments will be valuable for accelerating its adoption in next-generation capacitive devices and other high-performance electronic systems

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#### Declaration

## **Consent for publication**

Not applicable

Availability of data

Data shall be made available on demand.

**Competing interests** 

The authors declared no conflict of interest

**Ethical Consideration** 

Not applicable

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# **Authors' Contributions**

Fatima Musa Lariski designed and performed the experiments, carried out the synthesis and characterization of the Ce-doped BaTiO<sub>3</sub> ceramics, analyzed the data, and drafted the manuscript. Hassan Abdulsalam supervised the research, contributed to data interpretation, provided critical revisions, and approved the final version of the manuscript for publication

